

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
40V	2.1m Ω @10V	150A
	2.9m Ω @4.5V	

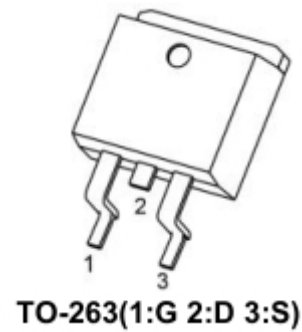
Feature

- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

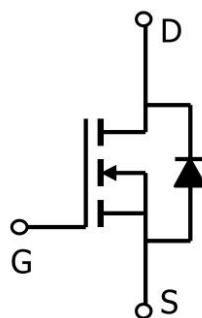
Application

- DC-DC Converter
- Power switching application

Package



Circuit diagram



Marking



40N02G =Device Code
****** =Week Code

Absolute maximum ratings

(T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ¹ (T _C =25°C, Package limit)	I _D	150	A
Pulsed Drain Current ²	I _{DM}	600	A
Single Pulse Avalanche Energy ³	E _{AS}	529	mJ
Total Power Dissipation ⁴ (T _C =25°C)	P _D	180	W
Thermal Resistance Junction-Case ¹	R _{θJC}	0.69	°C/W
Storage Temperature Range	T _{STG}	-55 to 150	°C
Operating Junction Temperature Range	T _J	-55 to 150	°C

Electrical characteristics

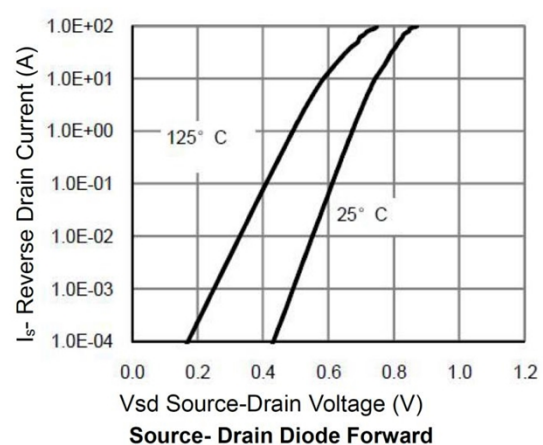
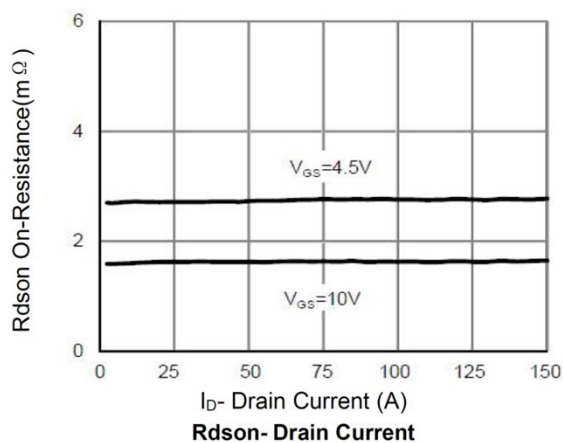
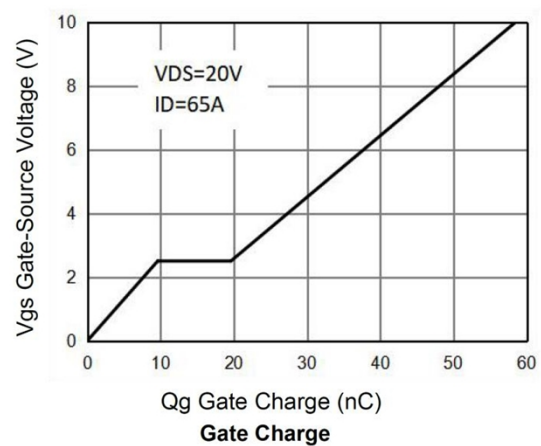
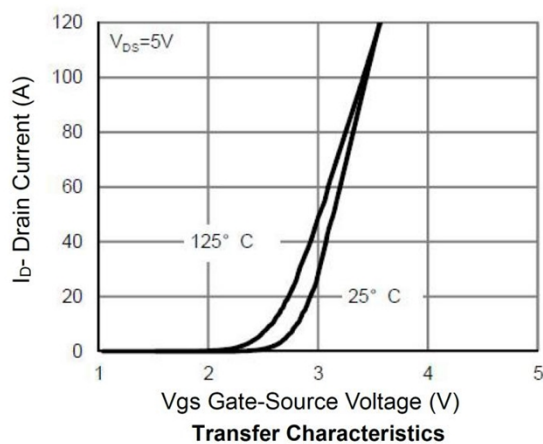
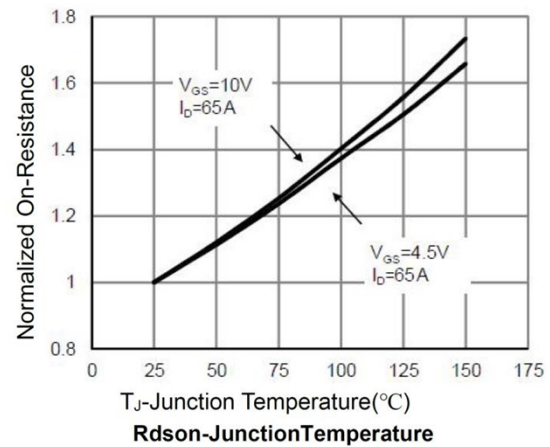
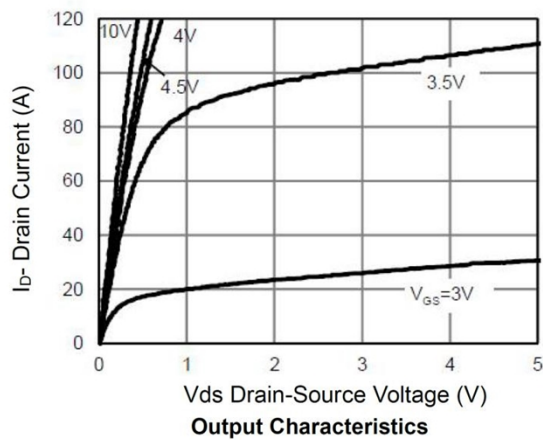
($T_A=25^{\circ}\text{C}$, unless otherwise noted)

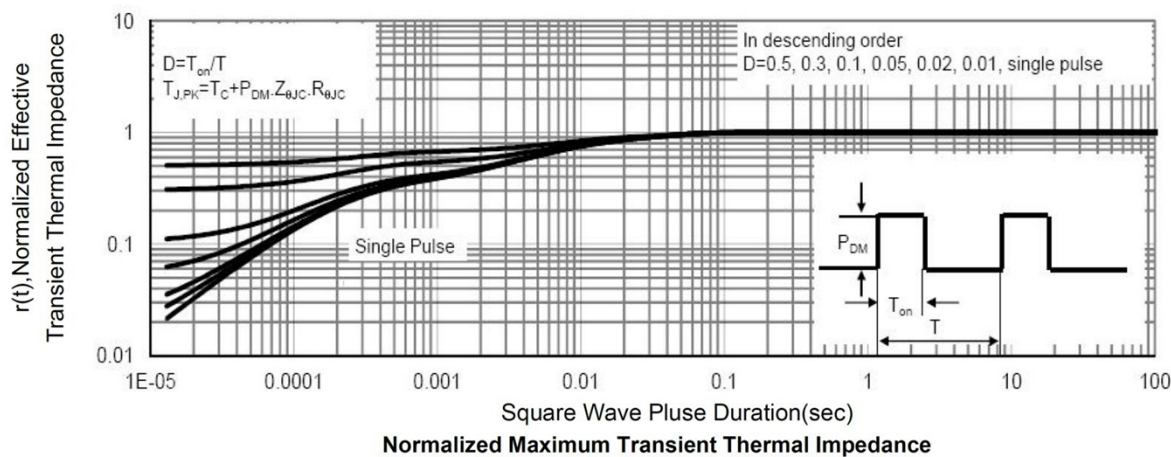
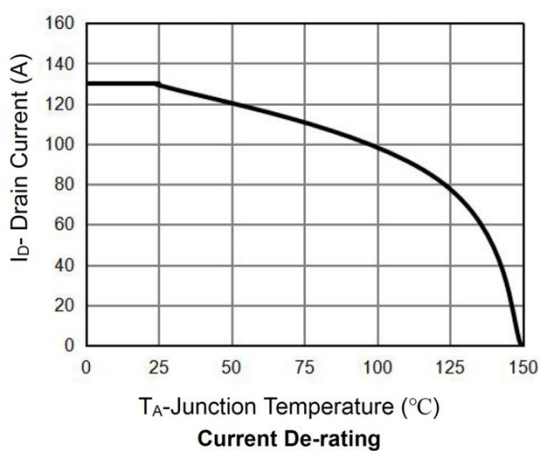
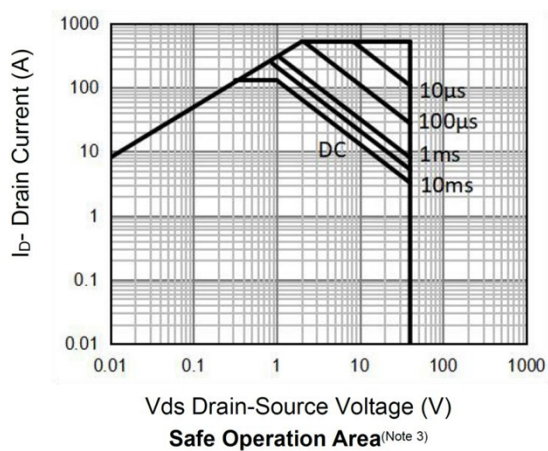
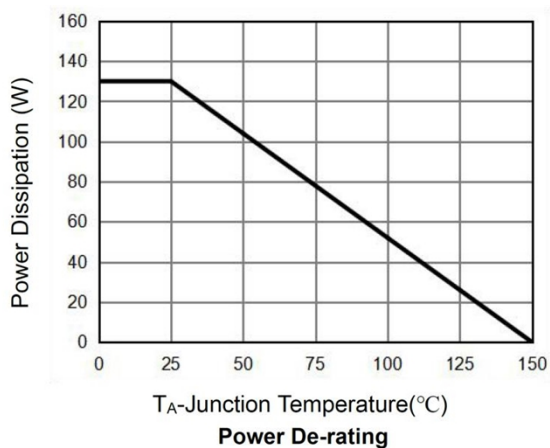
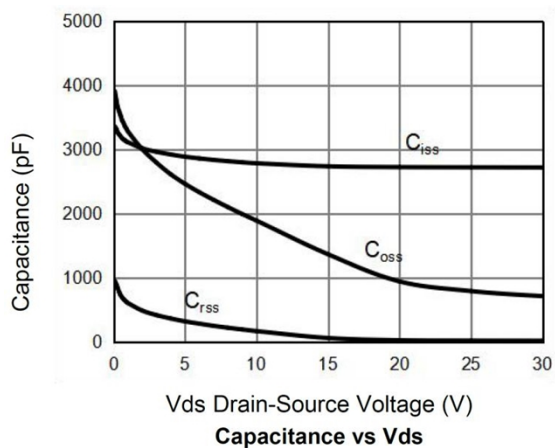
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV (BR)DSS	V _{GS} = 0V, I _D =250μA	40			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =32V,V _{GS} = 0V			1	uA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V , V _{DS} =0V			±100	uA
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Static Drain-Source On-Resistance ²	R _{DS(on)}	V _{GS} =10V, I _D =30A		2.1	2.65	mΩ
		V _{GS} =4.5V, I _D =20A		2.9	3.9	
Dynamic Characteristics						
Input Capacitance	C _{iSS}	V _{DS} =20V, V _{GS} =0V, f=1MHz		3485		pF
Output Capacitance	C _{OSS}			1208		
Reverse Transfer Capacitance	C _{rSS}			59		
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} =20V, V _{DS} =10V, I _D =65A		57		pF
Gate-Source Charge	Q _{gs}			9.5		
Gate-Drain Charge	Q _{gd}			11		
Turn-On Delay Time	T _{d(on)}	V _{DD} =20V, V _{GS} =10V, R _G =1.6Ω, I _D =65A		10		nS
Rise Time	T _r			3		
Turn-Off Delay Time	T _{d(off)}			35		
Fall Time	T _f			4		
Diode Characteristics						
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =20A,			1.2	V

Note:

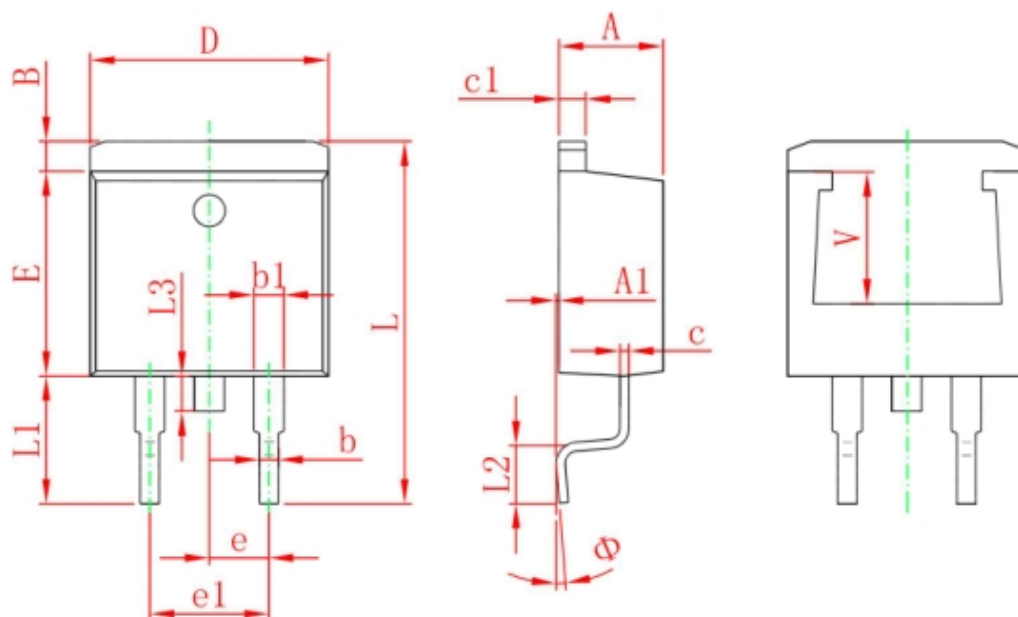
1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is $V_{DD}=20V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$
4. The power dissipation is limited by 150°C junction temperature

Typical Characteristics





TO-263 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
Φ	0°	8°	0°	8°
V	5.600 REF.		0.220 REF.	